Features

- Trench LV MOSFET Technology
- ESD HBM Class 2
- High Density Cell Design For Low $R_{DS(ON)}$
- Moisture Sensitivity Level 1
- Halogen Free. “Green” Device (Note1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

N-Channel MOSFET

Maximum Ratings

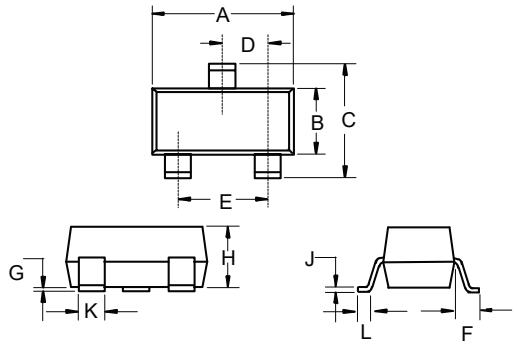
- Operating Junction Temperature Range: -55°C to +150°C
- Storage Temperature: -55°C to +150°C
- Thermal Resistance: 430°C/W Junction to Ambient(Note2)

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	60	V
Gate-Source Volltage		V_{GS}	±20	V
Continuous Drain Current	T_A=25°C	I_D	0.23	A
	T_A=100°C		0.14	
Pulsed Drain Current(Note3)		I_{DM}	0.92	A
Total Power Dissipation(Note4)		P_D	0.29	W

Note:

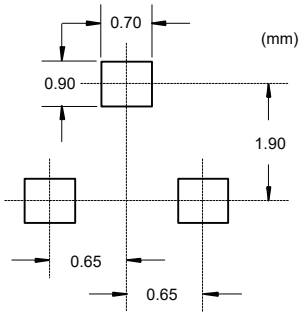
1. Halogen free "Green” products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
2. The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper， in a still air environment with T_A =25°C.
3. Repetitive rating; pulse width limited by max. junction temperature.
4. P_D is based on max. junction temperature, using junction-ambient thermal resistance.

SOT-323S

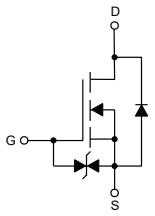


DIMENSIONS					
DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.071	0.087	1.80	2.20	
B	0.045	0.053	1.15	1.35	
C	0.078	0.087	2.00	2.20	
D	0.026		0.65		TYP.
E	0.047	0.055	1.20	1.40	
F	0.021		0.525		TYP.
G	0.000	0.004	0.00	0.10	
H	0.035	0.039	0.90	1.00	
J	0.004	0.010	0.10	0.25	
K	0.006	0.016	0.15	0.40	
L	0.010	0.018	0.26	0.46	

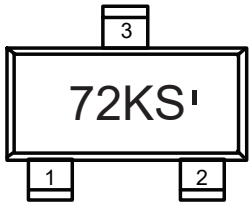
Suggested Solder Pad Layout



Internal Structure and Marking Code



1. GATE
2. SOURCE
3. DRAIN



Electrical Characteristics @ 25°C (Unless Otherwise Specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D=250μA	60			V
Gate-Source Leakage Current	I_{GSS}	V_{DS}=0V, V_{GS} =±20V			±10	μA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=48V, V_{GS}=0V			1	μA
Gate-Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=1mA	1.0	1.5	2.0	V
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=10V, I_D=500mA		1.8	2.5	Ω
		V_{GS}=4.5V, I_D=200mA		2.0	3.0	
Gate Resistance	R_g	f=1 MHz, Open drain		100		Ω
Diode Characteristics						
Continuous Body Diode Current	I_S				0.23	A
Diode Forward Voltage	V_{SD}	V_{GS}=0V, I_S=300mA			1.2	V
Reverse Recovery Time	t_{rr}	I_F=0.3A, dI_F/dt=100A/μs		11		ns
Reverse Recovery Charge	Q_{rr}			2.6		nC
Dynamic Characteristics						
Input Capacitance	C_{iss}	V_{DS}=25V,V_{GS}=0V,f=1MHz		15		pF
Output Capacitance	C_{oss}			3		
Reverse Transfer Capacitance	C_{rss}			2		
Total Gate Charge	Q_g	V_{DS}=30V,V_{GS}=10V,I_D=0.3A		0.9		nC
Gate-Source Charge	Q_{gs}			0.15		
Gate-Drain Charge	Q_{gd}			0.25		
Turn-On Delay Time	$t_{d(on)}$	V_{DD}=50V, V_{GS}=10V, R_G=50Ω, I_D=0.3A		3		ns
Turn-On Rise Time	t_r			3.8		
Turn-Off Delay Time	$t_{d(off)}$			10		
Turn-Off Fall Time	t_f			30		

Curve Characteristics

Fig.1 - Typical Output Characteristics

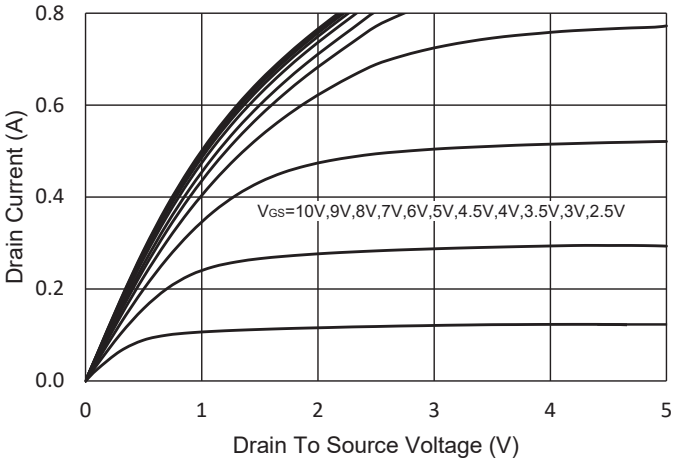


Fig. 2 - Transfer Characteristics

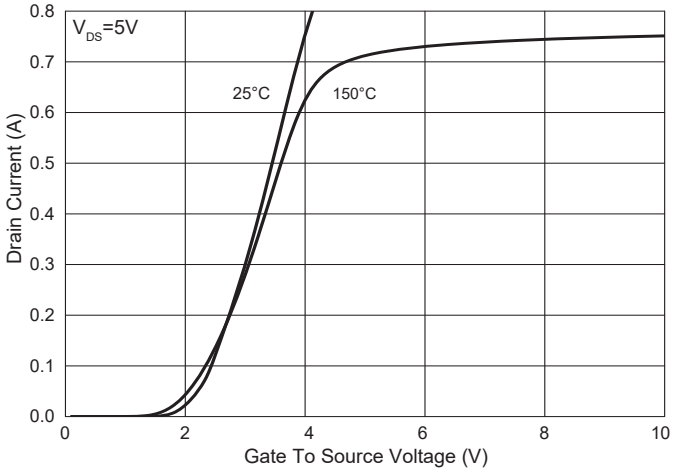


Fig. 3 - $R_{DS(ON)}$—V_{GS}

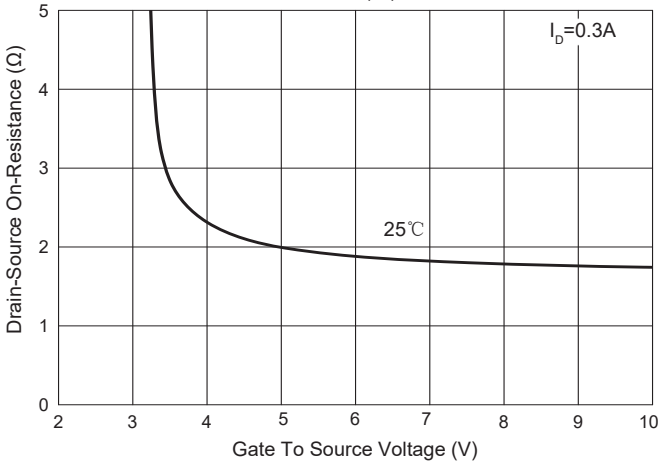


Fig. 4 - $R_{DS(ON)}$—I_D

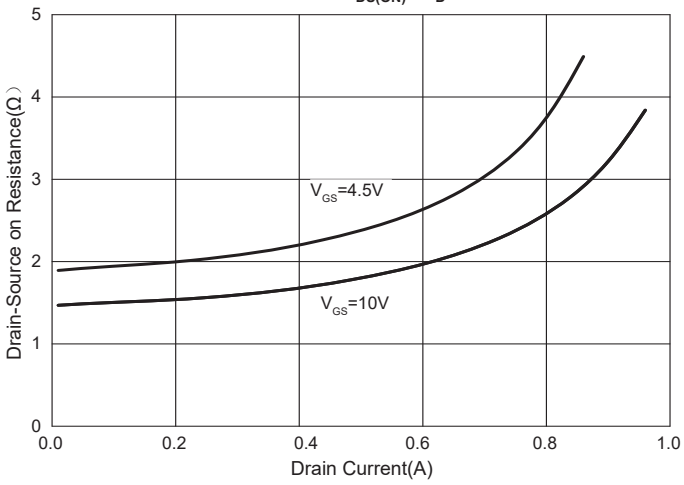


Fig. 5 - Capacitance Characteristics

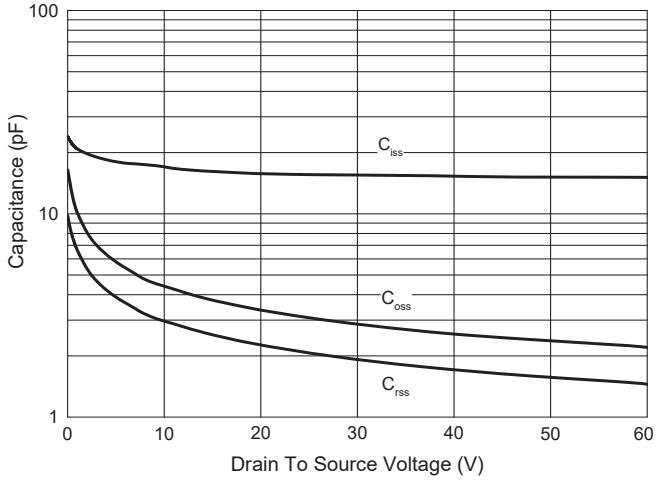
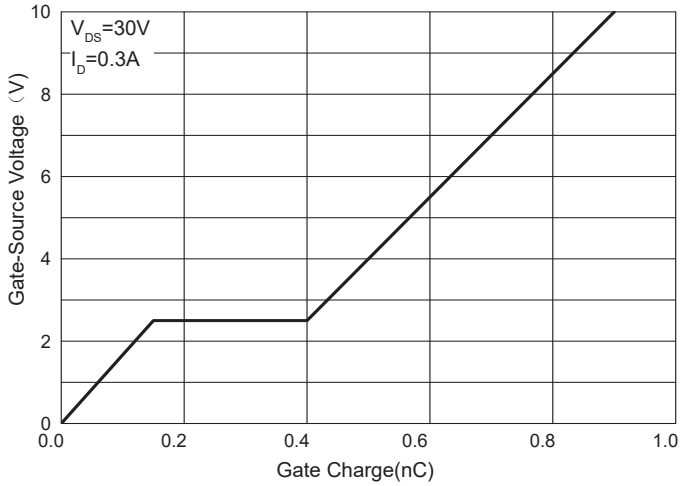


Fig. 6 - Gate Charge



Curve Characteristics

Fig.7 - Normalized Threshold Voltage

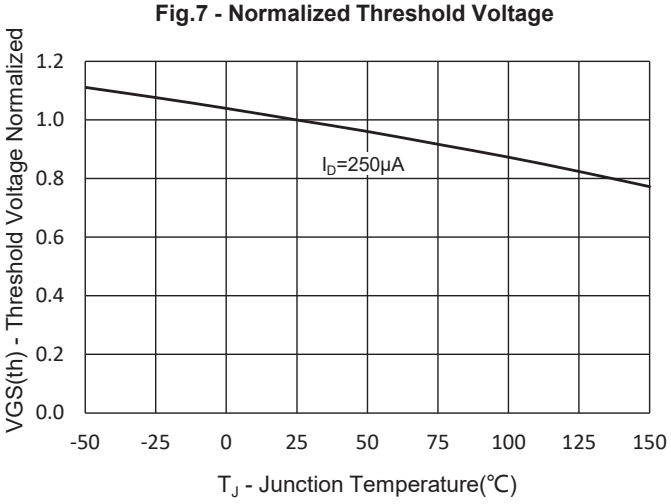


Fig.8 - Normalized On Resistance Characteristics

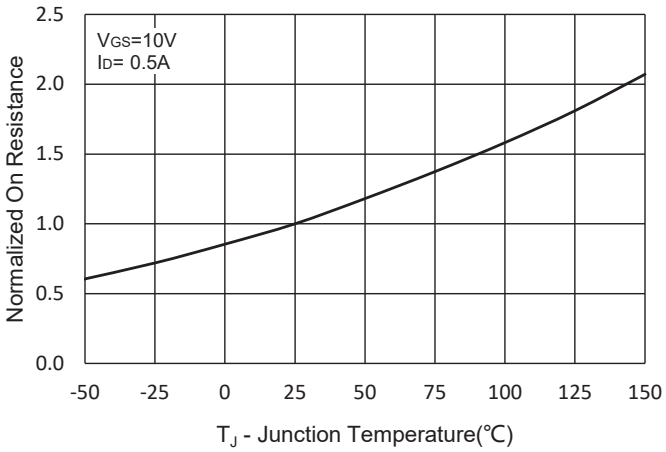


Fig.9 - I_S - V_{SD}

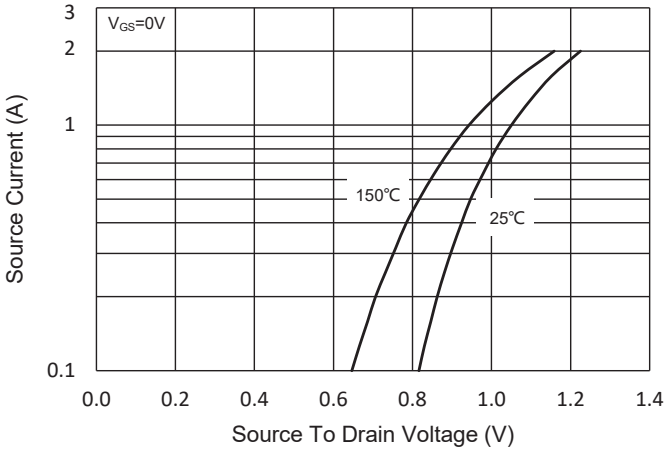


Fig. 10 - Drain Current

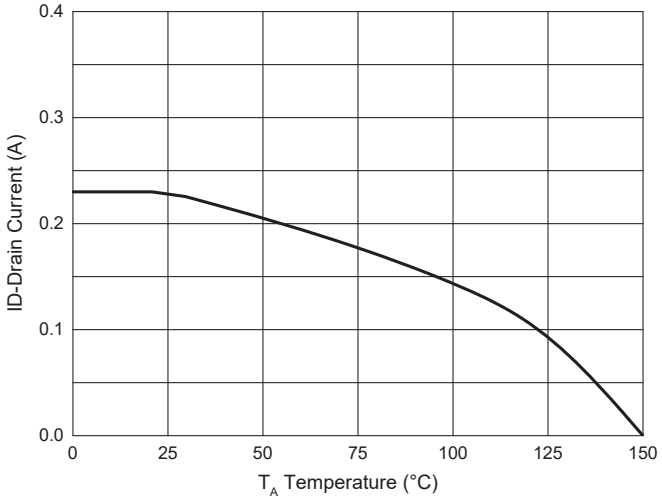
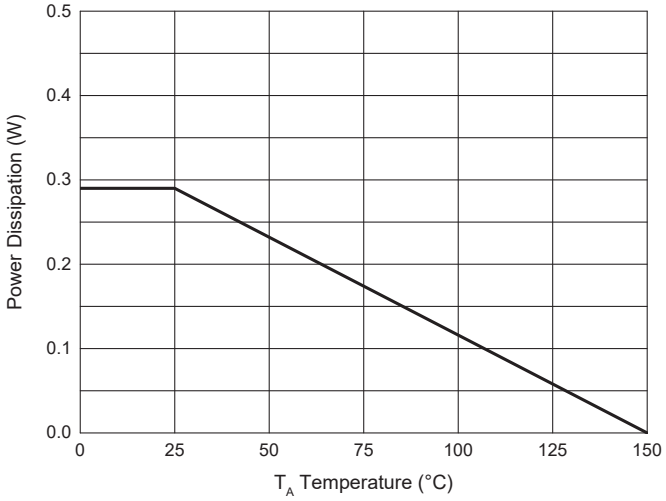


Fig. 11 - PD Dissipation



Curve Characteristics

Fig. 12 - Safe Operation Area

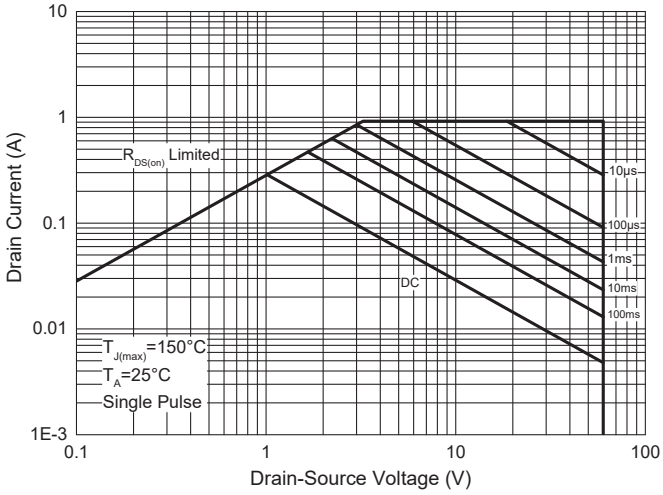
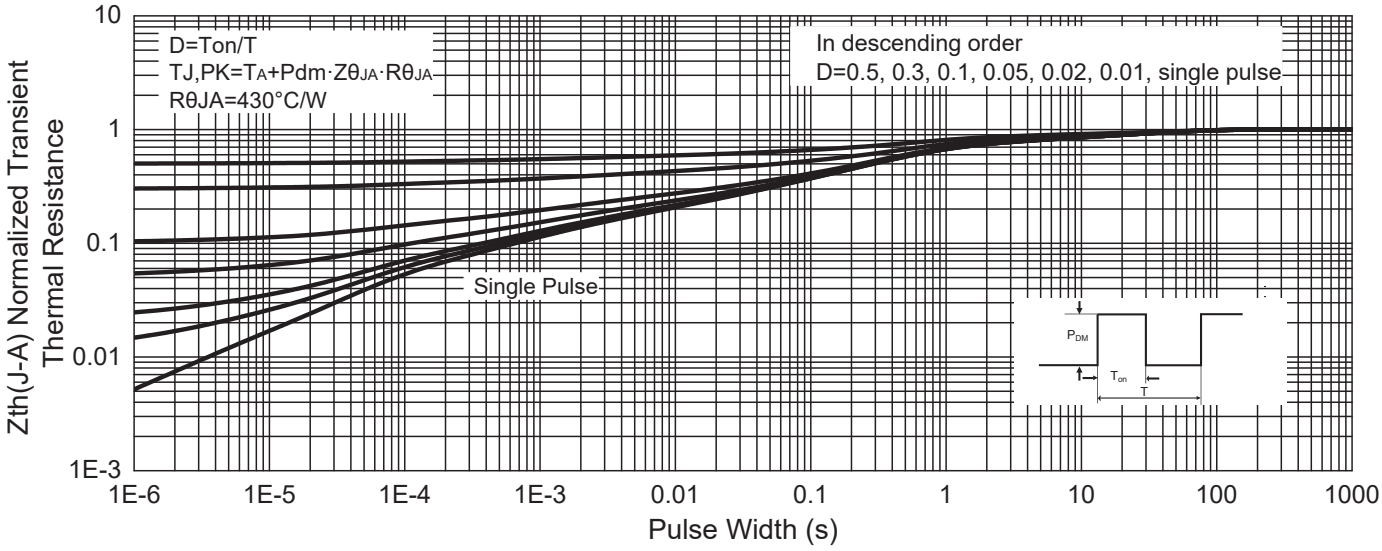


Fig. 13 - Normalized Transient Thermal Impedance



Ordering Information

Device	Packing
Part Number-TP	Tape&Reel: 3Kpcs/Reel